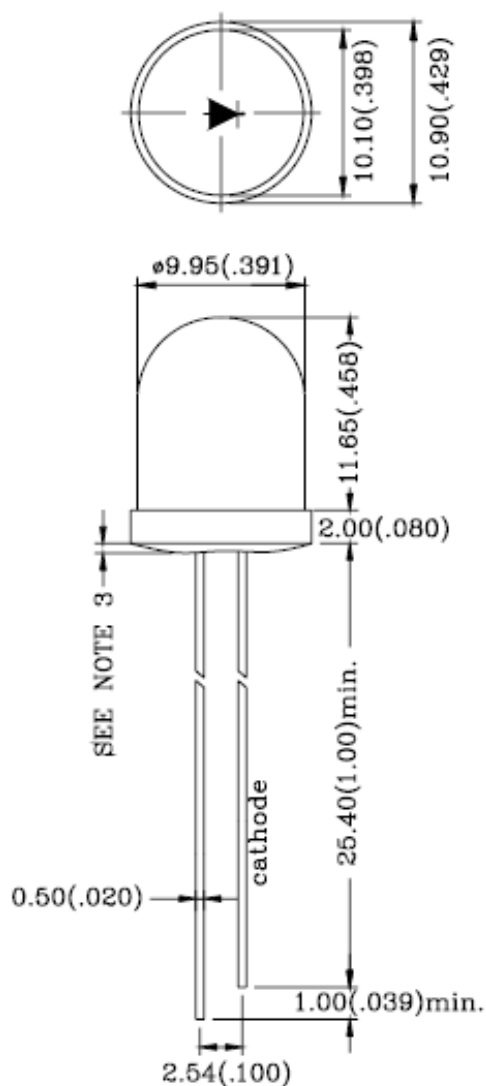


PACKAGE DIMENSIONS



Note:

1. All Dimensions are in millimeters.
2. Tolerance is $\pm 0.25\text{mm}$ (0.010 ") Unless otherwise specified.
3. Protruded resin under flange is 1.5mm (0.059 ") max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specification are subject to change without notice

FEATURES

- * 10.0mm DIA LED LAMP
- * LOW POWER CONSUMPTION.
- * I.C. COMPATIBLE.
- * LONG LIFE-SOLIDSTATE.

CHIP MATERIALS

- * Dice Material : GaAsP/GaP
- * Light Color : YELLOW
- * Lens Color : YELLOW DIFFUSED

ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

SYMBOL	PARAMETER	YELLOW	UNIT
PAD	Power Dissipation Per Chip	85	mW
VR	Reverse Voltage Per Chip	5	V
IAF	Continuous Forward Current Per Chip	30	mA
IPF	Peak Forward Current Per Chip (Duty—0.1,1KHz)	80	mA
—	Derating Linear From 25°C Per Chip	0.40	mA/°C
Topr	Operating Temperature Range	-25°C to 85°C	
Tstg	Storage Temperature Range	-40°C to 85°C	
Lead Soldering Temperature (1.6mm(0.063 inch) From Body) 260°C ± 5°C for 5 Seconds			

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
VF	Forward Voltage	IF = 20mA		2.15	2.8	V
IR	Reverse Current	VR = 5V			100	μA
λD	Dominant Wavelength	IF = 20mA		586		nm
Δλ	Spectral Line Half-Width	IF = 20mA		35		nm
2θ1/2	Half Intensity Angle	IF = 20mA		150		deg
Iv	Luminous Intensity	IF = 20mA		30		mcd

